

Description

The BUK7240-100A uses advanced trench technology

to provide excellent R_{DS(ON)}, low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



General Features

 $V_{DS} = 100V I_{D} = 30A$

 $R_{DS(ON)}$ < 48m Ω @ V_{GS} =10V



Battery protection

Load switch N-Channel MOSFET

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
BUK7240-100A	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Rating	Units	
V _{DS}	Drain-Source Voltage	100	V	
Vgs	Gate-Source Voltage	±20	V	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	30	Α	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	13	А	
Ідм	Pulsed Drain Current ²	80	Α	
EAS	Single Pulse Avalanche Energy ³	30	mJ	
P _D @T _C =25°C	Total Power Dissipation ⁴	42	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
Rejc	Thermal Resistance Junction-Case ¹	3.6	°C/W	



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Charac	cteristic	,				
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Charac	cteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.5	2.2	V
	Static Drain-Source on-Resistance	V _{GS} =10V, I _D =10A	-	37	48	mΩ
$R_{DS(on)}$		V _{GS} =4.5V, I _D =6A	-	39	55	mΩ
Dynamic (Characteristics				•	
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V,	-	1964	-	pF
Coss	Output Capacitance		-	90	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	74	-	pF
Qg	Total Gate Charge	V _{DS} =80V, I _D =20A,	-	20	-	nC
Q _{gs}	Gate-Source Charge		-	3.1	-	nC
Q_{gd}	Gate-Drain("Miller") Charge	V _{GS} =4.5V	-	14	-	nC
Switching	Characteristics					
$t_{d(on)}$	Turn-on Delay Time		-	11	-	ns
t _r	Turn-on Rise Time	V_{DS} =80V, I_{D} =20A, R_{G} =3.1 Ω , V_{GS} =4.5V	-	91	-	ns
t _{d(off)}	Turn-off Delay Time		-	40	-	ns
t _f	Turn-off Fall Time		-	71	-	ns
Drain-Sou	rce Diode Characteristics and Maxim	um Ratings				
Is	Maximum Continuous Drain to Source Diode Forward Current		-	-	27	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	80	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =20A	-	-	1.2	٧
trr	Body Diode Reverse Recovery Time	I -20A	-	64	-	ns
Qrr	Body Diode Reverse Recovery Charge	l _F =20A, dl/dt=100A/μs	-	152	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

- 2. EAS condition : T_J=25 $^{\circ}\text{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω ,I_AS= 11A
- 3. Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%



Typical Performance Characteristics

Figure1: Output Characteristics

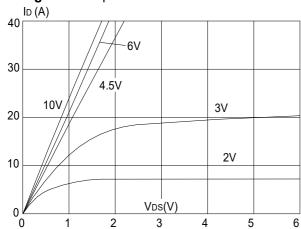


Figure 2: Typical Transfer Characteristics

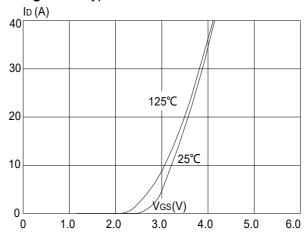


Figure 3:On-resistance vs. Drain Current

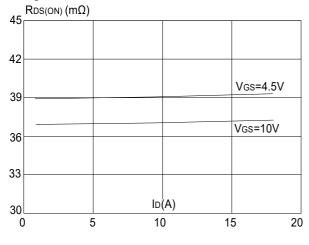


Figure 4: Body Diode Characteristics

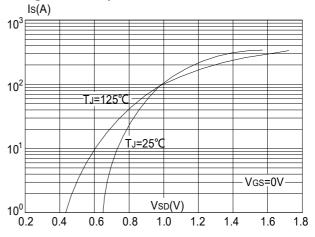


Figure 5: Gate Charge Characteristics

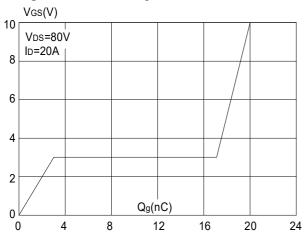


Figure 6: Capacitance Characteristics

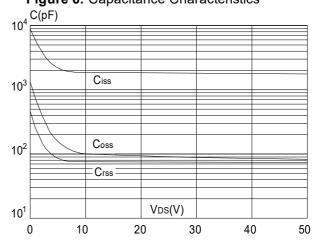




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

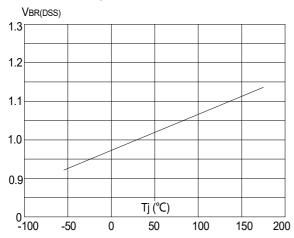


Figure 9: Maximum Safe Operating Area

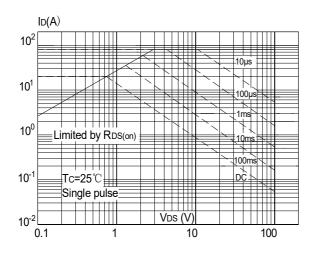


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

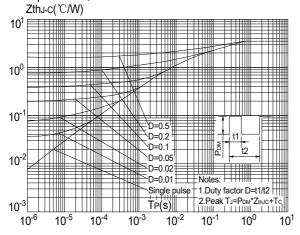


Figure 8: Normalized on Resistance vs. Junction Temperature

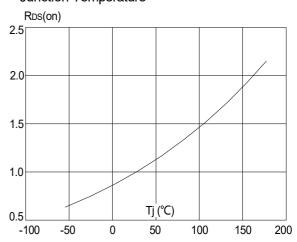
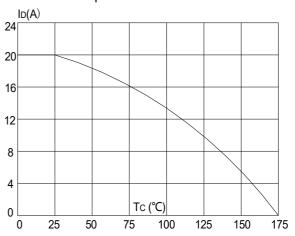
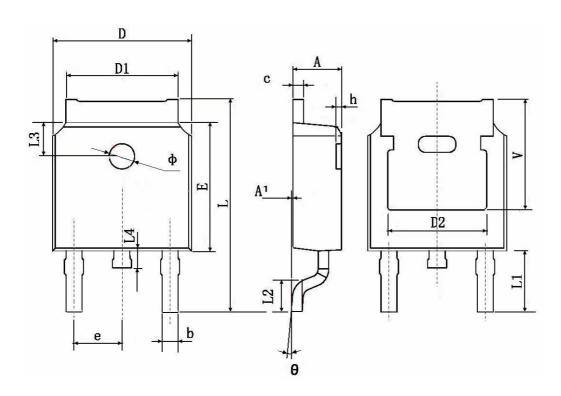


Figure 10: Maximum Continuous Drain Current vs. Case Temperature





TO-252-2L Package Information



Compleal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211 TYP.		



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